

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED MESA TYPE

2SC5149

HORIZONTAL DEFLECTION OUTPUT FOR MEDIUM RESOLUTION
DISPLAY, COLOR TV

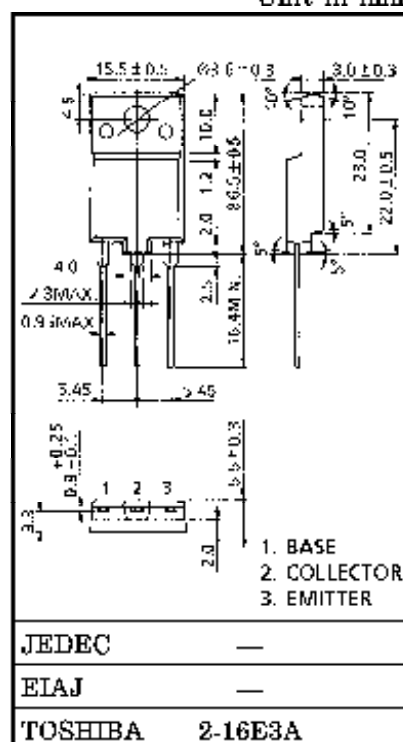
HIGH SPEED SWITCHING APPLICATIONS

- High Speed : $t_f = 0.2 \mu s$ (Typ.)
- High Voltage : $V_{CBO} = 1500 V$
- Low Saturation Voltage : $V_{CE(sat)} = 5 V$ (Max.)
- Built-in Damper Type
- Collector Metal (Fin) is Fully Covered with Mold Resin.

MAXIMUM RATINGS ($T_c = 25^\circ C$)

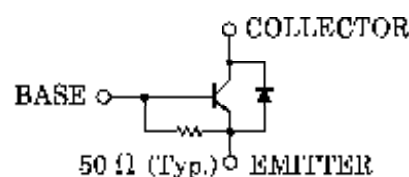
CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	1500	V
Collector-Emitter Voltage		V_{CEO}	600	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current	DC	I_C	8	A
	Pulse	I_{CP}	16	
Base Current		I_B	4	A
Collector Power Dissipation ($T_c = 25^\circ C$)		P_C	50	W
Junction Temperature		T_j	150	$^\circ C$
Storage Temperature Range		T_{slg}	$-55 \sim 150$	$^\circ C$

Unit in mm



Weight : 5.5 g (Typ.)

EQUIVALENT CIRCUIT



96100-1451

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● The information contained herein is subject to change without notice.

ELECTRICAL CHARACTERISTICS ($T_a = 25^\circ\text{C}$)

CHARACTERISTIC		SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current		I_{CBO}	$V_{CB} = 1500\text{ V}, I_E = 0$	—	—	1	mA
Emitter Cut-off Current		I_{EBO}	$V_{EB} = 5\text{ V}, I_C = 0$	66	—	200	mA
Emitter-Base Breakdown Voltage		V_{EBO}	$I_E = 400\text{ mA}, I_C = 0$	5	—	—	V
DC Current Gain		$h_{FE}(1)$	$V_{CE} = 5\text{ V}, I_C = 1\text{ A}$	8	—	25	
		$h_{FE}(2)$	$V_{CE} = 5\text{ V}, I_C = 5\text{ A}$	3.8	—	8.0	
Collector-Emitter Saturation Voltage		$V_{CE(sat)}$	$I_C = 5\text{ A}, I_B = 1.3\text{ A}$	—	—	5	V
Base-Emitter Saturation Voltage		$V_{BE(sat)}$	$I_C = 5\text{ A}, I_B = 1.3\text{ A}$	—	1.0	1.3	V
Forward Voltage (Damping Diode)		$-V_F$	$I_F = 5\text{ A}$	—	1.35	1.8	V
Transition Frequency		f_T	$V_{CE} = 10\text{ V}, I_C = 0.1\text{ A}$	—	2	—	MHz
Collector Output Capacitance		C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	110	—	pF
Switching Time	Storage Time	t_{stg}	$I_{CP} = 6\text{ A}, I_{B1}(\text{end}) = 1.1\text{ A}, f_H = 31.5\text{ kHz}$	—	4	6	μs
	Fall Time	t_f		—	0.2	0.5	

